

Silicon PNP Power Transistors

2SB1190

DESCRIPTION

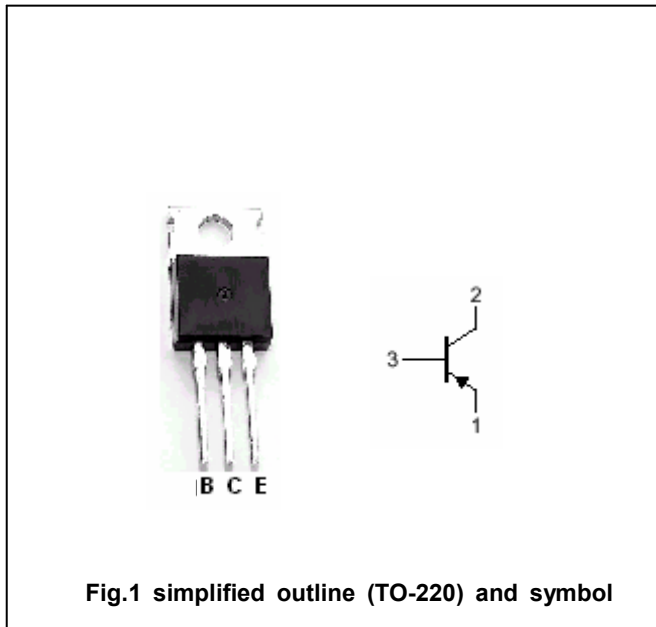
- With TO-220 package
- High V_{CEO}
- Large P_C
- Complement to type 2SD1772

APPLICATIONS

- Power amplifier
- TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-2	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.4	W
		$T_C=25^\circ\text{C}$	25	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-5mA, I _B =0	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.5mA, I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-300mA; V _{CE} =-10V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-200V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-100mA; V _{CE} =-10V	60		240	
h _{FE-2}	DC current gain	I _C =-300mA; V _{CE} =-10V	50			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V, f=1MHz		35		pF
f _T	Transition frequency	I _C =-100mA; V _{CE} =-10V		20		MHz

◆ h_{FE-1} Classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE

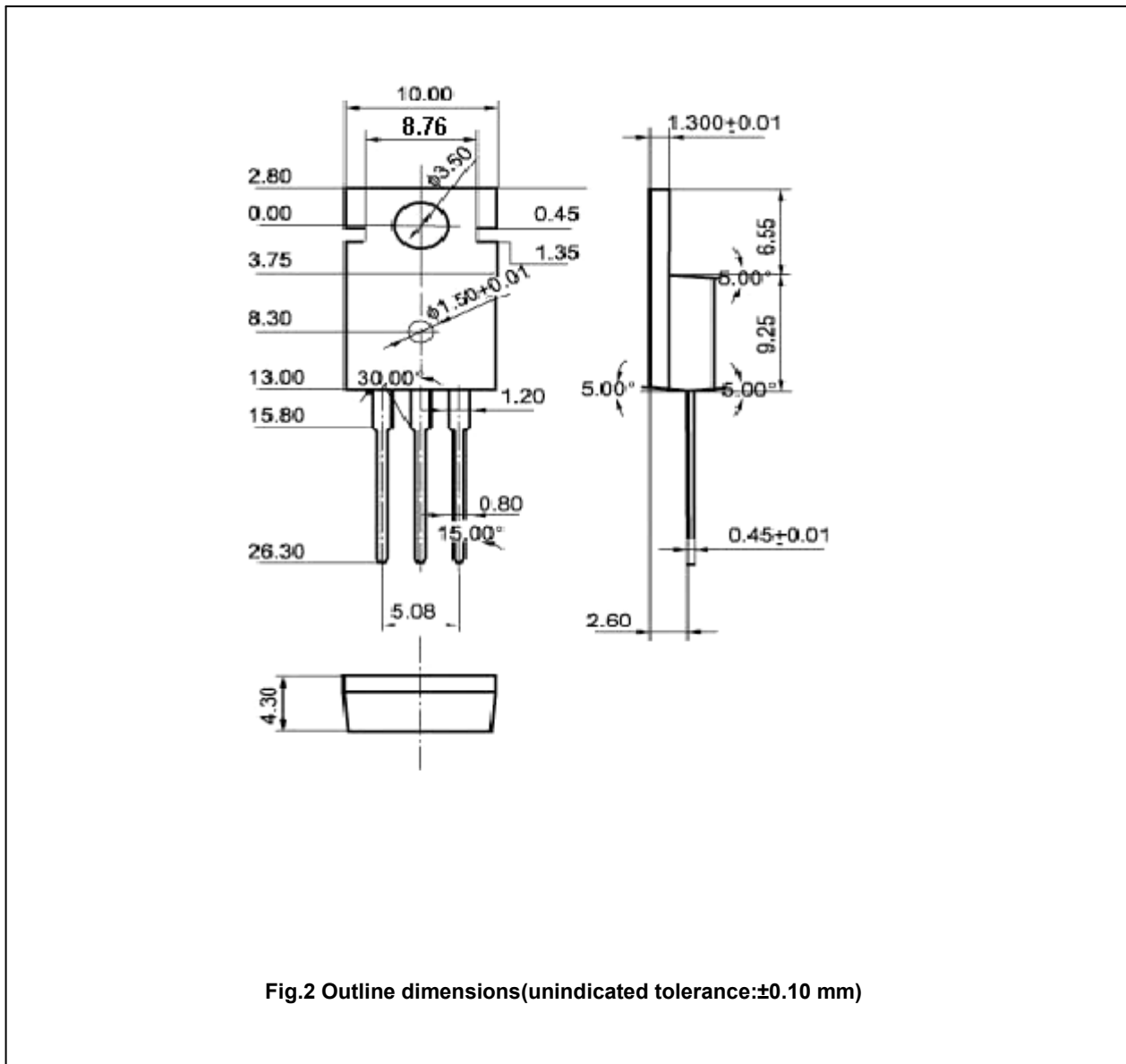


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)